Current Transducer HAT 200..1500-S

For the electronic measurement of currents: DC, AC, pulsed, mixed, with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).



Primary nominal Primary current r.m.s. current measuring range 4)		Туре	Туре	
I _{PN} (A)				
200	± 600	HAT 200-S		
400	± 1200 HAT 40)0-S	
500	± 1500	HAT 500-S	HAT 500-S HAT 600-S HAT 750-S HAT 800-S HAT 1000-S HAT 1200-S	
600	± 1800			
750	± 2250			
800 1000	± 2400 ± 3000			
1200	± 3000 ± 3000			
1500	± 3000	HAT 1500-S		
V _c	Supply voltage (± 5 %) ⁴⁾	± 15	V	
	Current consumption	± 15	mA	
Ř _{is}	Isolation resistance @ 500 VDC	> 1000	MΩ	
V _{OUT}	Output voltage @ $\pm \mathbf{I}_{PN}$, $\mathbf{R}_{L} = 10 \text{ k}\Omega$, $\mathbf{T}_{A} = 25^{\circ}\text{C}$	± 4	V	
R _{OUT}	Output internal resistance	100	Ω	
R,	Load resistance	> 10	kΩ	
-	uracy-Dynamic performance data			
	·			
x	Accuracy @ I_{PN} , $T_{A} = 25^{\circ}C$ (without offset)			
X e	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹⁾ (0 $\pm \mathbf{I}_{PN}$)			
X e	Accuracy @ I_{PN} , $T_{A} = 25^{\circ}C$ (without offset)		of $\mathbf{I}_{_{\mathrm{PN}}}$	
X e _l V _{oe}	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset) Linearity error ¹⁾ (0 ± I_{PN}) Electrical offset voltage, $T_A = 25^{\circ}C$	<±1 %	of $\mathbf{I}_{_{\mathrm{PN}}}$	
X Cel V _{oe}	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹) (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$;	<±1 %	of I _{PN} mV	
Х С _L V _{OE} V _{OH}	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹⁾ (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$; after an excursion of 1 x \mathbf{I}_{PN}	< ± 1 % < ± 20 < ± 10	of I _{PN} mV mV	
Х С _L V _{ое} V _{он}	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹⁾ (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$; after an excursion of 1 x \mathbf{I}_{PN} Thermal drift of \mathbf{V}_{OE}	< ± 1 % < ± 20 < ± 10	of I _{PN} of I _{PN} mV mV/K %/K	
X е _L V _{ое} V _{он} V _{от} TC e _G	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹ (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$; after an excursion of 1 x \mathbf{I}_{PN} Thermal drift of \mathbf{V}_{OE} Thermal drift of the gain (% of reading)	< ± 1 % < ± 20 < ± 10 < ± 1	of I _{PN} mV mV/K %/K	
X е _L V _{ое} V _{он} V _{от} TC e _G	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹⁾ (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$; after an excursion of 1 x \mathbf{I}_{PN} Thermal drift of \mathbf{V}_{OE}	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1	of I _{PP} mV mV/K %/K μs	
Х Ф _L V _{ое} V _{он} TC C f	Accuracy @ \mathbf{I}_{PN} , $\mathbf{T}_{A} = 25^{\circ}C$ (without offset) Linearity error ¹) (0 $\pm \mathbf{I}_{PN}$) Electrical offset voltage, $\mathbf{T}_{A} = 25^{\circ}C$ Hysteresis offset voltage @ $\mathbf{I}_{P} = 0$; after an excursion of 1 x \mathbf{I}_{PN} Thermal drift of \mathbf{V}_{OE} Thermal drift of the gain (% of reading) Response time @ 90% of \mathbf{I}_{P}	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1 < 5	of I _{PN} mV mV/K	
X Ф _L V _{оЕ} V _{оН} TC C t, f Gen	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset) Linearity error ¹) (0 ± I_{PN}) Electrical offset voltage, $T_A = 25^{\circ}C$ Hysteresis offset voltage @ $I_P = 0$; after an excursion of 1 x I_{PN} Thermal drift of V_{OE} Thermal drift of the gain (% of reading) Response time @ 90% of I_P Frequency bandwidth ²) (- 3 dB)	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1 < 5	of I _{PN} mV mV/K %/K μs kHz	
X \mathbf{e}_{L} \mathbf{v}_{oe} \mathbf{v}_{oH} \mathbf{v}_{oH} $\mathbf{r}_{\mathbf{e}}$ Gen \mathbf{T}_{A}	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset) Linearity error ¹) (0 $\pm I_{PN}$) Electrical offset voltage, $T_A = 25^{\circ}C$ Hysteresis offset voltage @ $I_P = 0$; after an excursion of 1 x I_{PN} Thermal drift of V_{OE} Thermal drift of the gain (% of reading) Response time @ 90% of I_P Frequency bandwidth ²) (- 3 dB)	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1 < 5 DC 25	of I _{PN} mV mV/K %/K μs kHz	
X Ф _L V _{оЕ} V _{оН} TC C f Gen T _A	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset) Linearity error ¹) (0 $\pm I_{PN}$) Electrical offset voltage, $T_A = 25^{\circ}C$ Hysteresis offset voltage @ $I_P = 0$; after an excursion of 1 x I_{PN} Thermal drift of V_{OE} Thermal drift of the gain (% of reading) Response time @ 90% of I_P Frequency bandwidth ²) (- 3 dB) Deral data Ambient operating temperature Ambient storage temperature HAT 200-S, HAT 500	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1 < 5 DC 25 - 10 + 80 01500-S - 15 + 85	of I _{PN} mV mV/K %/K μs kHz	
Х Ф _L V _{ое} V _{он} TC C f	Accuracy @ I_{PN} , $T_A = 25^{\circ}C$ (without offset) Linearity error ¹) (0 $\pm I_{PN}$) Electrical offset voltage, $T_A = 25^{\circ}C$ Hysteresis offset voltage @ $I_P = 0$; after an excursion of 1 x I_{PN} Thermal drift of V_{OE} Thermal drift of the gain (% of reading) Response time @ 90% of I_P Frequency bandwidth ²) (- 3 dB)	< ± 1 % < ± 20 < ± 10 < ± 1 < ± 0.1 < 5 DC 25	of I _{PN} mV mV/K %/K μs kHz	

Notes : ¹⁾ Linearity data exclude the electrical offset.

- ²⁾ Please refer to derating curves in the technical file to avoid excessive core heating at high frequency.
- ³⁾ Please consult characterisation report for more technical details and application advice.
- ⁴⁾ Operating at $\pm 12V \le Vc < \pm 15V$ will reduce the measuring range.





I_{PN} = 200..1500 A

 $V_{out} = \pm 4 V$

Features

- · Hall effect measuring principle
- Galvanic isolation between primary and secondary circuit
- Isolation voltage 3000 V
- Low power consumption
- Extended measuring range $(3 \times I_{PN})$
- Insulated plastic case recognized according to UL 94-V0

Advantages

- · Easy mounting
- Small size and space saving
- Only one design for wide current ratings range
- · High immunity to external interference.

Applications

- DC motor drives
- Switched Mode Power Supplies (SMPS)
- AC variable speed drives
- Uninterruptible Power Supplies (UPS)
- · Battery supplied applications
- · Power supplies for welding applications

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Current Transducer HAT 200..1500-S

Isolation characteristics					
	Rated Voltage	1000	V		
	with IEC 61010-1 standards and following conditions				
	- Reinforced insulation				
	- Over voltage category III				
	- Pollution degree 2				
	- Heterogeneous field				
V _d	R.m.s. voltage for AC isolation test, 50 Hz, 1 mn	3	kV		
dČp	Creepage distance	> 11	mm		
dCl	Clearance distance	> 11	mm		
CTI	Comparative Tracking Index (Group IIIa)	275			

Notes :

LEM reserves the right to carry out modifications on its transducers, in order to improve them, without previous notice.

Top view æ Max. 23 4 6 5 Positive current flow 9 65 30.5 x 40.5 15.5 4 Molex 5045-04A Pins arrangement 1 2 3 4 (+) (-) Output 0V Front view

Dimensions HAT 200..1500-S (in mm. 1 mm = 0.0394 inch)

Mechanical characteristics

- General tolerance
- Transducer fastening
- Connection of secondary

Remarks

- I_s is positive when I_p flows in the direction of the arrow.
- Temperature of the primary conductor should not exceed 100°C.

± 1 mm

screws.

bus bar with M4

Molex 5045-04A

All slots Ø 4.5 mm

Safety By base-plate or on

This transducer must be used in electric/electronic equipment with respect to applicable standards and safety requirements in accordance with the following manufacturer's operating instructions.



Caution, risk of electrical shock

When operating the transducer, certain parts of the module can carry hazardous voltage (eg. primary busbar, power supply). Ignoring this warning can lead to injury and/or cause serious damage.

This transducer is a built-in device, whose conducting parts must be inaccessible after installation.

A protective housing or additional shield could be used. Main supply must be able to be disconnected.

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